

# ROHS V

v03.0514

## **Typical Applications**

The HMC609LC4 is ideal for:

- Fixed Microwave
- Test & Measurement Equipment
- Radar & Sensors
- Military & Space

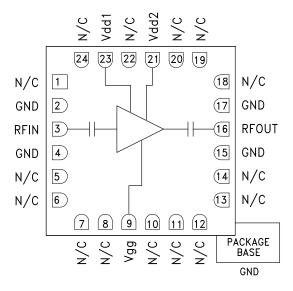
## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 4 GHz

HMC609LC4

#### Features

Excellent Gain Flatness: ±0.4 dB High Gain: 20 dB Low Noise Figure: 3.5 dBm Output IP3: +36.5 dBm 50 Ohm Matched & DC Blocked RF I/Os RoHS Compliant 4 x 4 mm SMT Package

#### Functional Diagram



### **General Description**

The HMC609LC4 is a GaAs PHEMT MMIC Low Noise Amplifier (LNA) which operates from 2 to 4 GHz. The HMC609LC4 features extremely flat performance characteristics including 20 dB of small signal gain, 3.5 dB of noise figure and output IP3 of +36.5 dBm across the operating band. This 50 Ohm matched amplifier does not require any external matching components. The HMC609LC4 is compatible with high volume surface mount manufacturing techniques, and the RF I/Os are DC blocked for further ease of integration.

#### Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd1 = Vdd2 = +6V, Idd1 + Idd2 = 170 mA<sup>[1]</sup>

Parameter	Min.	Тур.	Max.	Units
Frequency Range	2 - 4		GHz	
Gain	17	20		dB
Gain Variation Over Temperature		0.015	0.02	dB/ °C
Noise Figure		3.5	5.5	dB
Input Return Loss		17		dB
Output Return Loss		15		dB
Output Power for 1 dB Compression (P1dB)	18.5	21.5		dBm
Saturated Output Power (Psat)		23		dBm
Output Third Order Intercept (IP3)		36.5		dBm
Supply Current (Idd1 + Idd2)		170	220	mA

Adjust Vgg between -1.5V to -0.5V (Typical -0.9V) to achieve total drain bias of 170mA

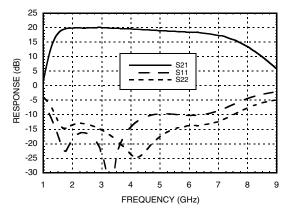
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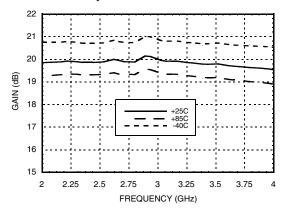
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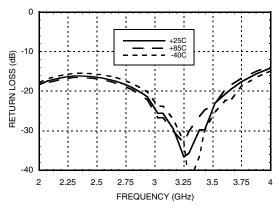
#### Broadband Gain & Return Loss<sup>[1]</sup>



Gain vs. Temperature [1]



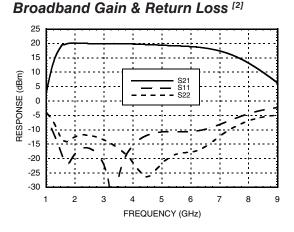
Input Return Loss vs. Temperature [1]



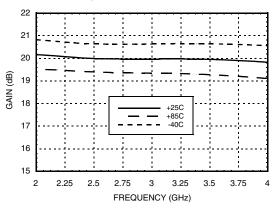
[1] Vdd = 6V [2] Vdd = 5V

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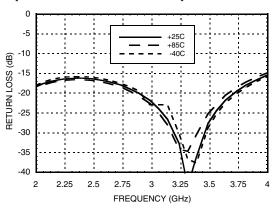
## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 4 GHz



#### Gain vs. Temperature [2]



Input Return Loss vs. Temperature [2]

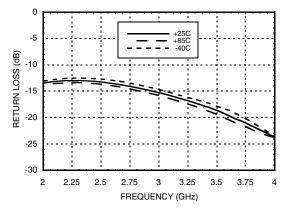




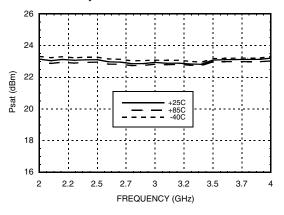
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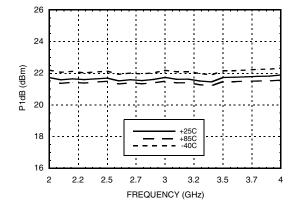
#### Output Return Loss vs. Temperature [1]



Psat vs. Temperature [1]



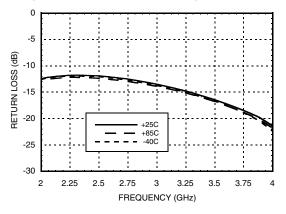
P1dB vs. Temperature [1]



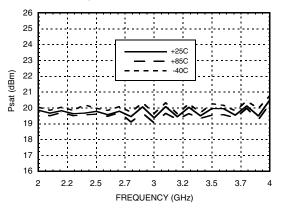
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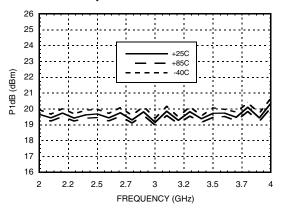
#### Output Return Loss vs. Temperature [2]



Psat vs. Temperature <sup>[2]</sup>



P1dB vs. Temperature <sup>[2]</sup>



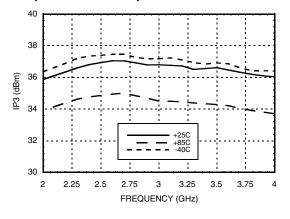
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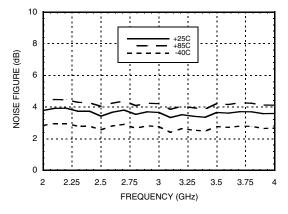
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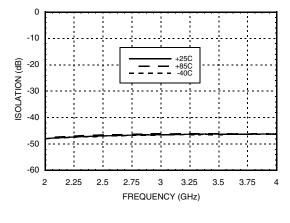
#### Output IP3 vs. Temperature [1]



Noise Figure vs. Temperature [1]



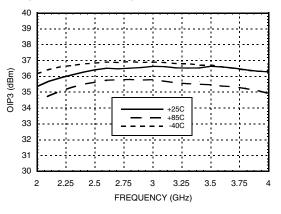
**Reverse Isolation vs. Temperature**<sup>[1]</sup>



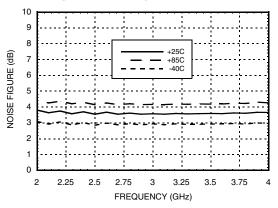
[1] Vdd = 6V [2] Vdd = 5V

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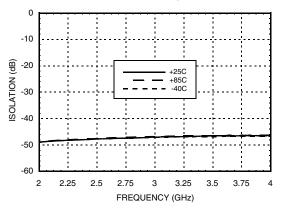
#### Output IP3 vs. Temperature [2]



#### Noise Figure vs. Temperature [2]



Reverse Isolation vs. Temperature [2]



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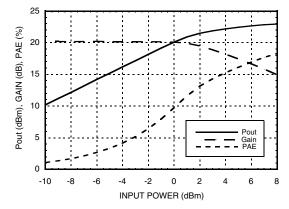




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## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 4 GHz

#### Power Compression @ 3 GHz



#### Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	7 Vdc	
RF Input Power (RFIN)(Vdd = +6.0 Vdc)	+15 dBm	
Channel Temperature	175 °C	
Continuous Pdiss (T= 85 °C) (derate 16.7 mW/°C above 85 °C)	1.1 W	
Thermal Resistance (channel to ground paddle)	60 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	

#### Typical Supply Current vs. Vdd

Vdd (V)	ldd (mA)
+5.5	160
+6.0	170
+6.5	180

Note: Amplifier will operate over full voltage range shown above



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AMPLIFIER, 2 - 4 GHz

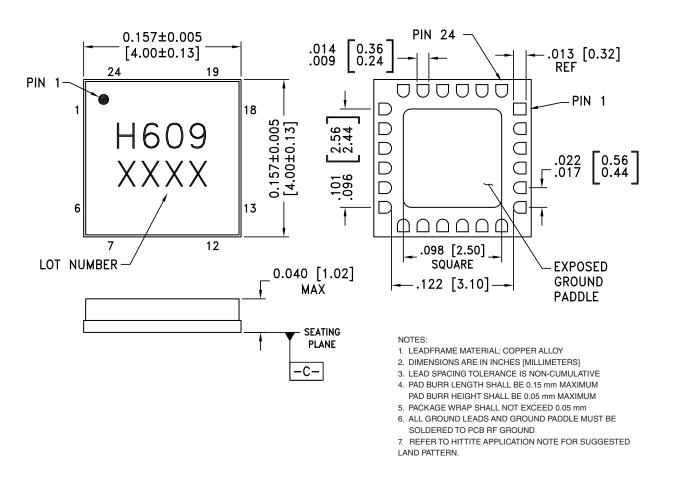
GaAs PHEMT MMIC LOW NOISE

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#### **Outline Drawing**

#### BOTTOM VIEW



#### **Package Information**

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking <sup>[2]</sup>
HMC609LC4	Alumina, White	Gold over Nickel	MSL3 <sup>[1]</sup>	H609 XXXX

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

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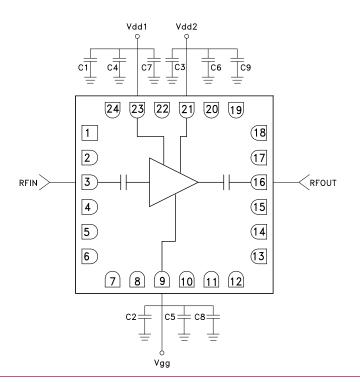
## GaAs PHEMT MMIC LOW NOISE AMPLIFIER, 2 - 4 GHz

#### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 5 - 8, 10 - 24, 18 - 20, 22, 24	N/C	This pin may be connected to RF/DC ground. Performance will not be affected.	
2, 4, 15, 17	GND	These pins and package bottom must also be connected to RF/DC ground.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	
9	Vgg	Gate supply voltage for the amplifier. (External bypass capacitors are required.)	Vgg o
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	○ RFOUT
21, 23	Vdd1, Vdd2	Power Supply Voltage for the amplifier. (External bypass capacitors are required.).	OVdd ↓ ↓ ↓ ↓

## **Application Circuit**

Component	Value
C1 - C3	100 pF
C4 - C6	1,000 pF
C7 - C9	2.2 µF



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